

'die-2-die' (D2D)
interfaces
operate
outside the
typical GPIO range

lower signal voltage & reduced drive current





For speed, D2D interfaces are designed with thin oxide transistors

but those are easily damaged during ESD events





The parasitic capacitance of ESD protection in traditional GPIOs is too high

for high bandwidth D2D interfaces





the standard I/O pads consume too much silicon area





ESD clamps integrated in traditional GPIOs are designed for >2kV HBM

while D2D interfaces only need a fraction of that.



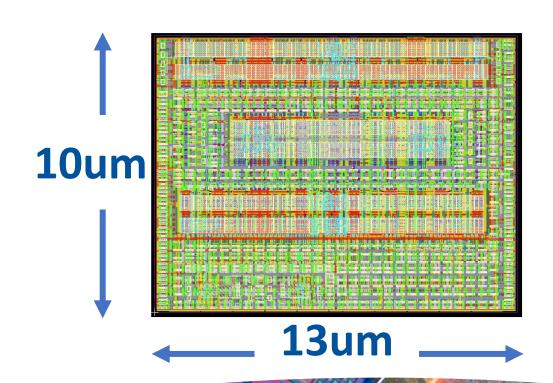
Sofics proven approach

- ESD protection of sensitive thin oxide circuits
- Protection for interfaces at 1V or lower
- ESD protection in smaller area
- Much reduced parasitic capacitance
- Scalable ESD robustness
- Proven on many fabs, processes



Example on 5nm FinFET

Full local protection for 0.9V I/O >100V HBM 14fF total capacitance





Reach out

 For more examples on other processes

To discuss your project



